

# PUMD15-Q

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

8 March 2023

**Product data sheet** 

### 1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH15 PNP/PNP complement: PUMB15

#### 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplified circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

### 3. Applications

- Low current peripheral driver
- Controlling IC inputs
- · Replacement of general purpose transistors in digital applications

#### 4. Quick reference data

#### Table 1. Quick reference data

Tubio II Quio	K reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or		·			'	
$V_{CEO}$	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)		[2]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[2]	8.0	1	1.2	

- [1] For the PNP transistor (TR2) with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2 006aaa143

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
PUMD15-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>			

# 7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD15-Q	D0%

[1] % = placeholder for manufacturing site code

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

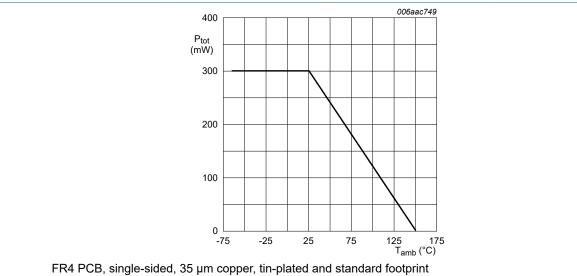
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or		'	<u> </u>		_
V <sub>CBO</sub>	collector-base voltage	open emitter	[1]	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	[1]	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	[1]	-	10	V
VI	input voltage	TR1 (NPN)		-10	30	V
		TR2 (PNP)		-30	10	V
Io	output current		[1]	-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	200	mW
Per device				'		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- For the PNP transistor (TR2) with negative polarity.
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



Per device: Power derating curve

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

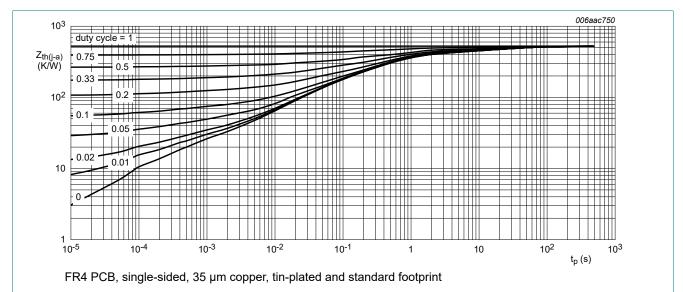


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 10. Characteristics

**Table 7. Characteristics** 

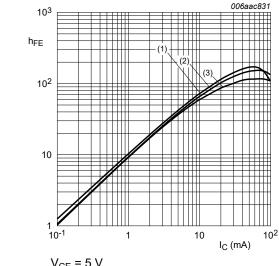
	Conditions		Min	Тур	Max	Unit
or						
collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	100	nA
collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	100	nA
current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C	[1]	-	-	5	μΑ
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	-	-	900	μΑ
DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C	[1]	30	-	-	
collector-emitter saturation voltage	$I_C$ = 10 mA; $I_B$ = 0.5 mA; $T_{amb}$ = 25 °C	[1]	-	-	150	mV
off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C	[1]	-	1.1	0.5	V
on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 20 mA; T <sub>amb</sub> = 25 °C	[1]	2.5	1.9	-	V
bias resistor 1 (input)		[2]	3.3	4.7	6.1	kΩ
bias resistor ratio		[2]	0.8	1	1.2	
collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	2.5	pF
transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	[3]	-	230	-	MHz
			'			
collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	-	3	pF
transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[3]	-	180	-	MHz
	collector-base breakdown voltage  collector-emitter breakdown voltage  collector-base cut-off current  collector-emitter cut-off current  emitter-base cut-off current  DC current gain  collector-emitter saturation voltage  off-state input voltage  on-state input voltage bias resistor 1 (input) bias resistor ratio  collector capacitance  transition frequency	collector-base breakdown voltage	collector-base breakdown voltage	collector-base breakdown voltage $I_C = 100  \mu A;  I_E = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         50           collector-emitter breakdown voltage $I_C = 2  mA;  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         50           collector-emitter breakdown voltage $V_{CB} = 50  V;  I_E = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         -           collector-base cut-off current $V_{CE} = 30  V;  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         -           collector-emitter cut-off current $V_{CE} = 30  V;  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         -           emitter-base cut-off current $V_{CE} = 30  V;  I_C = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         -           DC current gain $V_{CE} = 5  V;  I_C = 10  mA;  T_{amb} = 25  ^{\circ}C$ [1]         -           collector-emitter saturation voltage $I_C = 10  mA;  I_B = 0.5  mA;  T_{amb} = 25  ^{\circ}C$ [1]         -           off-state input voltage $V_{CE} = 5  V;  I_C = 100  \mu A;  T_{amb} = 25  ^{\circ}C$ [1]         -           on-state input voltage $V_{CE} = 0.3  V;  I_C = 20  mA;  T_{amb} = 25  ^{\circ}C$ [1]         2.5           bias resistor 1 (input)         [2]         3.3           bias resistor ratio         [2]         0.8           collector cap	collector-base breakdown voltage $I_C = 100  \mu A;  I_E = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         50         -           collector-emitter breakdown voltage $I_C = 2  \text{mA};  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         50         -           collector-base cut-off current $V_{CB} = 50  V;  I_E = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         -         -           collector-emitter cut-off current $V_{CE} = 30  V;  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         -         -           emitter-base cut-off current $V_{CE} = 30  V;  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ [1]         -         -           DC current gain $V_{CE} = 5  V;  I_C = 10  \text{mA};  T_{amb} = 25  ^{\circ}C$ [1]         -         -           collector-emitter saturation voltage $I_C = 10  \text{mA};  I_B = 0.5  \text{mA};  T_{amb} = 25  ^{\circ}C$ [1]         -         -           off-state input voltage $V_{CE} = 5  V;  I_C = 100  \mu A;  T_{amb} = 25  ^{\circ}C$ [1]         -         -           on-state input voltage $V_{CE} = 5  V;  I_C = 100  \mu A;  T_{amb} = 25  ^{\circ}C$ [1]         -         1.1           bias resistor 1 (input)         [2]         3.3         4.7           bias resistor ratio $V_{CB} = 10  V;  I_C = 10  M;  I_C = 0  A;  I_C =$	$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$

<sup>[1]</sup> For the PNP transistor (TR2) with negative polarity.

<sup>[2]</sup> See section "Test information" for resistor calculation and test conditions.

<sup>[3]</sup> Characteristics of built-in transistor

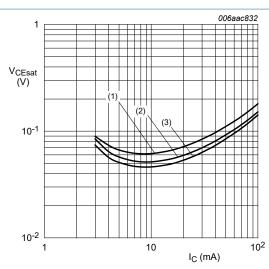
#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$



 $V_{CE} = 5 V$ (1)  $T_{amb} = 100 °C$ 

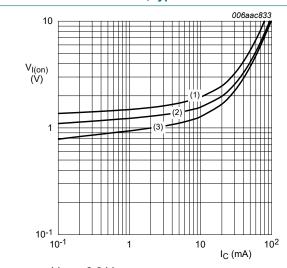
(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



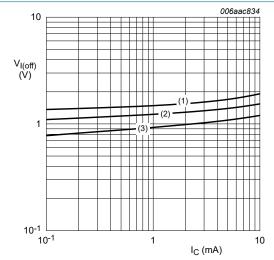
 $V_{CE} = 0.3 V$ 

(1) T<sub>amb</sub> = -40 °C

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$ 

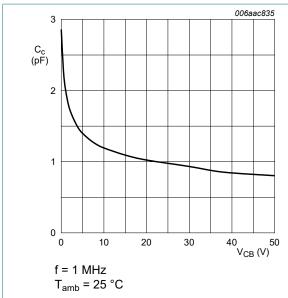
(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

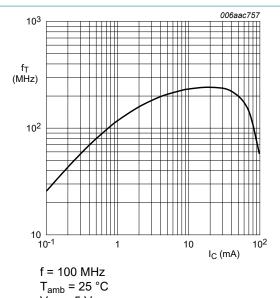
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

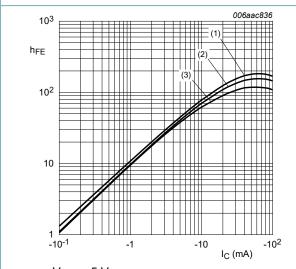


TR1 (NPN): Collector capacitance as a function Fig. 7. of collector-base voltage; typical values



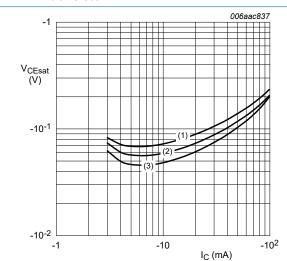
 $T_{amb}$  = 25 °C  $V_{CE}$  = 5 V

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



 $V_{CE}$  = -5 V $(1) T_{amb} = 100 °C$ (2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = -40 \, ^{\circ}C$ 

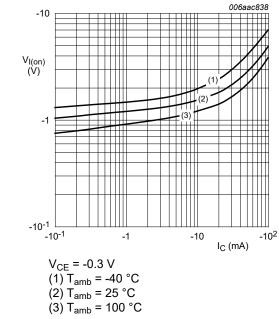
Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values



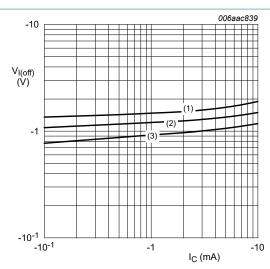
 $I_{\rm C}/I_{\rm B} = 20$ (1) T<sub>amb</sub> = 100 °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$



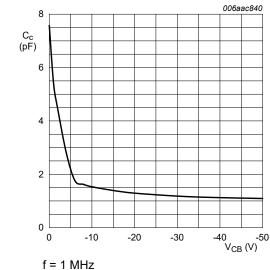
of collector current; typical values



V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C

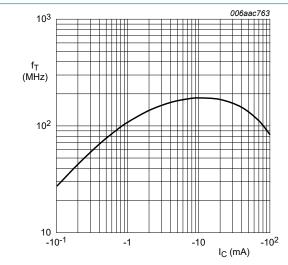
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 11. TR2 (PNP): On-state input voltage as a function | Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz

 $T_{amb}$  = 25 °C

 $V_{CE} = -5 V$ 

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

#### 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

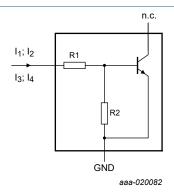


Fig. 15. NPN transistor: Resistor test circuit

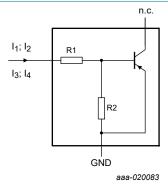


Fig. 16. PNP transistor: Resistor test circuit

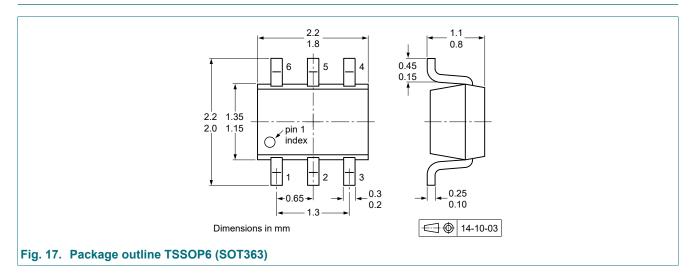
#### **Resistor test conditions**

**Table 8. Resistor test conditions** 

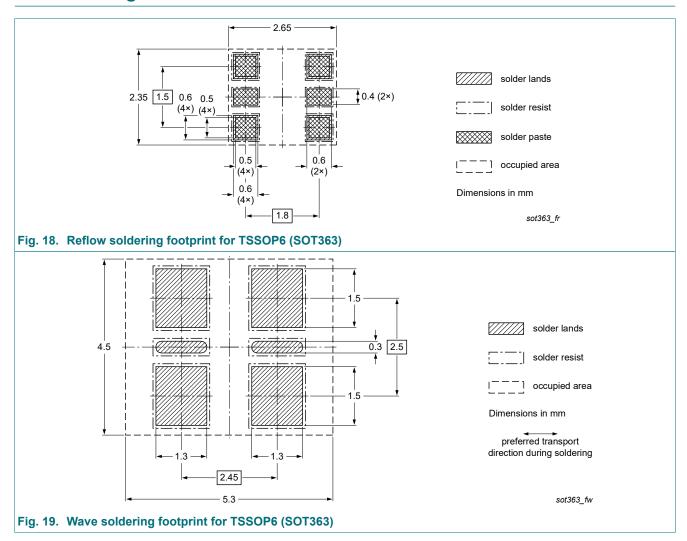
PUMD15-Q	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14	
TR1 (NPN)	4.7	4.7	600 μΑ	700 µA	-600 μA	-700 μA	
TR2 (PNP)	4.7	4.7	-600 μΑ	-700 μA	600 µA	700 μΑ	

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 12. Package outline



# 13. Soldering



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD15-Q v.1	20230308	Product data sheet	-	-

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PUMD15-Q

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

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For more information, please visit: http://www.nexperia.com
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